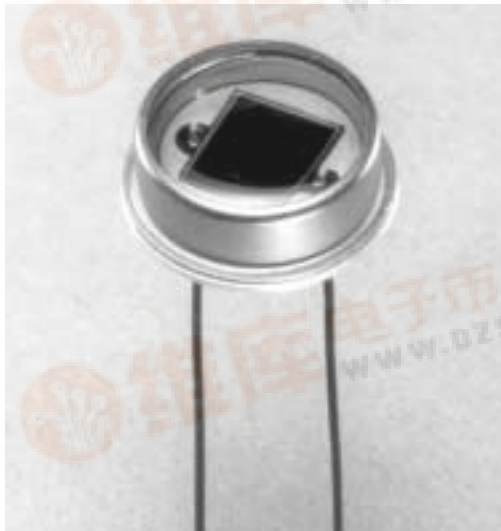
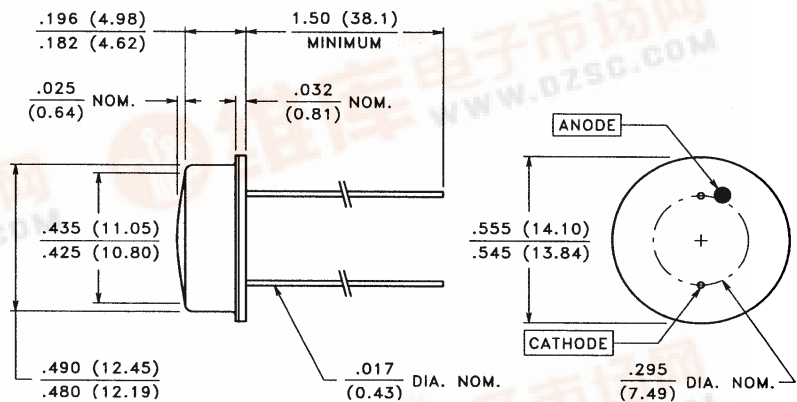


VTB Process Photodiodes

VTB6061BH



PACKAGE DIMENSIONS inch (mm)



CASE 15 TO-8 HERMETIC
CHIP ACTIVE AREA: .058 in² (37.7 mm²)

PRODUCT DESCRIPTION

Large area planar silicon photodiode in a "flat" window, dual lead TO-8 package. The package incorporates an infrared rejection filter. Cathode is common to the case. These diodes have very high shunt resistance and have good blue response.

ABSOLUTE MAXIMUM RATINGS

Storage Temperature: -40°C to 110°C
Operating Temperature: -40°C to 110°C

ELECTRO-OPTICAL CHARACTERISTICS @ 25°C (See also VTB curves, pages 21-22)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	VTB6061BH			UNITS
			Min.	Typ.	Max.	
I _{SC}	Short Circuit Current	H = 100 fc, 2850 K	26	35		μA
TC I _{SC}	I _{SC} Temperature Coefficient	2850 K		.02	.08	%/°C
V _{OC}	Open Circuit Voltage	H = 100 fc, 2850 K		420		mV
TC V _{OC}	V _{OC} Temperature Coefficient	2850 K		-2.0		mV/°C
I _D	Dark Current	H = 0, V _R = 2.0 V			2.0	nA
R _{SH}	Shunt Resistance	H = 0, V = 10 mV		.10		GΩ
TC R _{SH}	R _{SH} Temperature Coefficient	H = 0, V = 10 mV		-8.0		%/°C
C _J	Junction Capacitance	H = 0, V = 0		8.0		nF
λ _{range}	Spectral Application Range		330		720	nm
λ _p	Spectral Response - Peak			580		nm
V _{BR}	Breakdown Voltage		2	40		V
θ _{1/2}	Angular Resp. - 50% Resp. Pt.			±55		Degrees
NEP	Noise Equivalent Power			1.0 x 10 ⁻¹³ (Typ.)		W/√Hz
D*	Specific Detectivity			6.1 x 10 ¹² (Typ.)		cm√Hz/W

